2SB766A TRANSISTOR(PNP)

FEATURES

- Large collector power dissipation P_C
- Complementary to 2SD874A

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-60	V
V_{CEO}	Collector-Emitter Voltage	-50	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-1	A
P_C	Collector Power Dissipation	500	mW
T_J,T_{stg}	Operation Junction and Storage Temperature Range	-55~150	℃

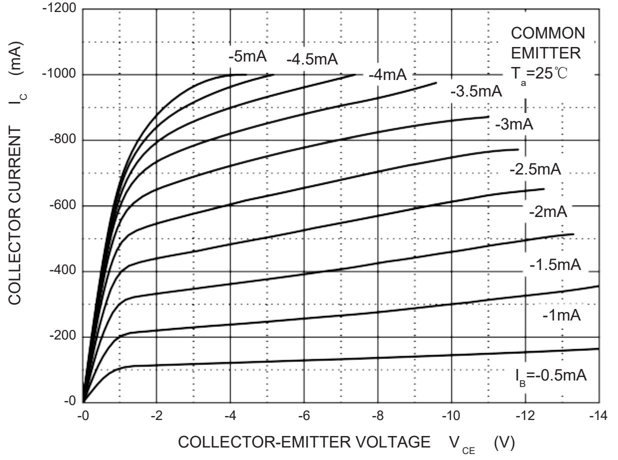
ELECTRICAL CHARACTERISTICS (T_a=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	Ic=-10μA,I_E=0	-60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	Ic=-2mA,I_B=0	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-10μA,I_C=0	-5			V
Collector cut-off current	I_{CBO}	V_{CB}=-20V,I_E=0			-0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=-4V,I_C=0			-0.1	μA
DC current gain	$h_{FE(1)}$	V_{CE}=-10V,I_C=-500mA	85		340	
	$h_{FE(2)}$	V_{CE}=-5V,I_C=-1A	50			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-500mA,I_B=-50mA		-0.2	-0.4	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C=-500mA,I_B=-50mA		-0.85	-1.2	V
Transition frequency	f_T	V_{CE}=-10V,I_C=-50mA,f=200MHz		200		MHz
Collector output capacitance	C_{ob}	V_{CB}=-10V,I_E=0,f=1MHz		20	30	pF

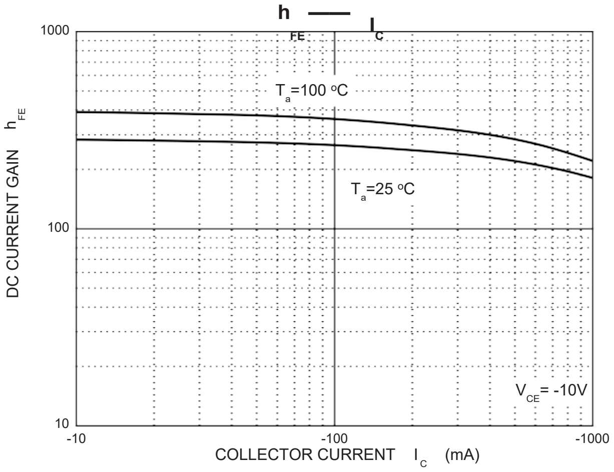
CLASSIFICATION OF $h_{FE(1)}$

Rank	Q	R	S
Range	85-170	120-240	170-340
MAKING	**BQ**	**BR**	**BS**

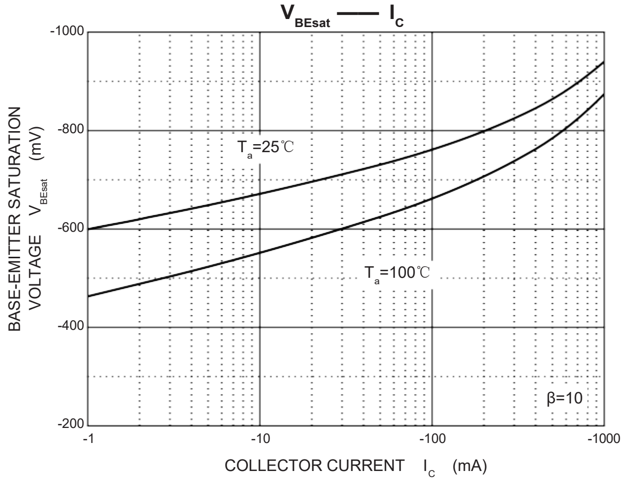
Static Characteristic



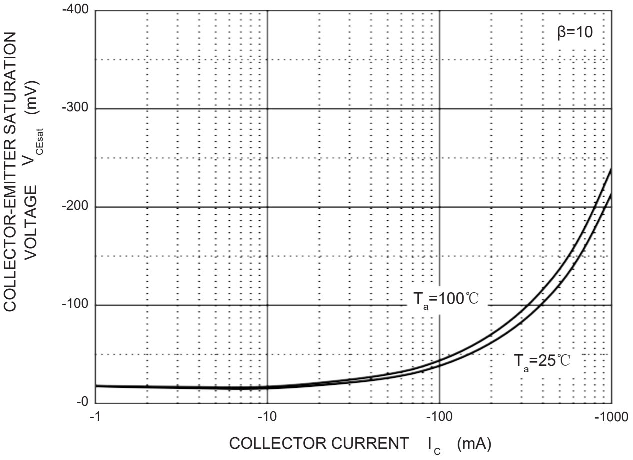
h_{FE} — I_C



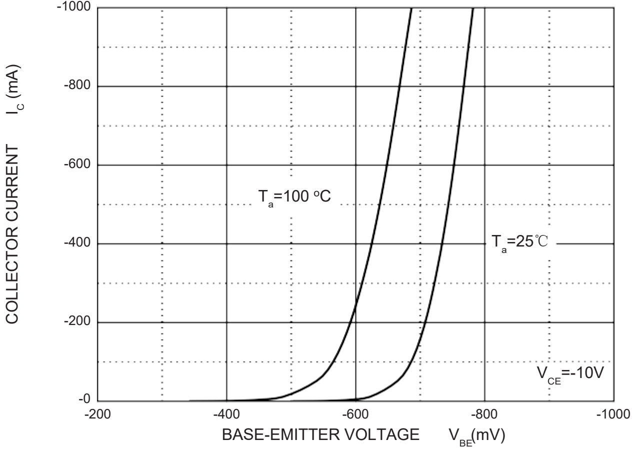
V_{BEsat} — I_C



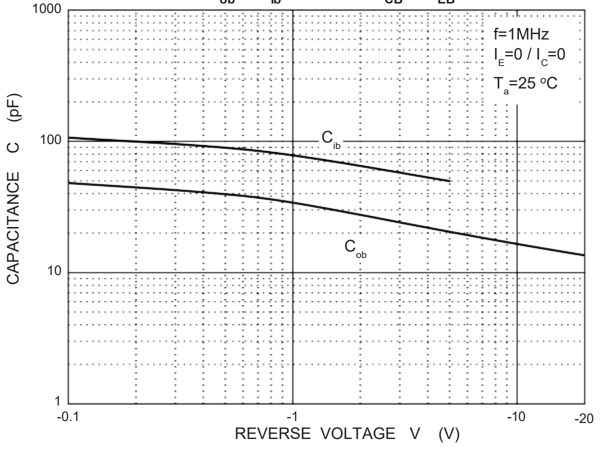
V_{CEsat} — I_C



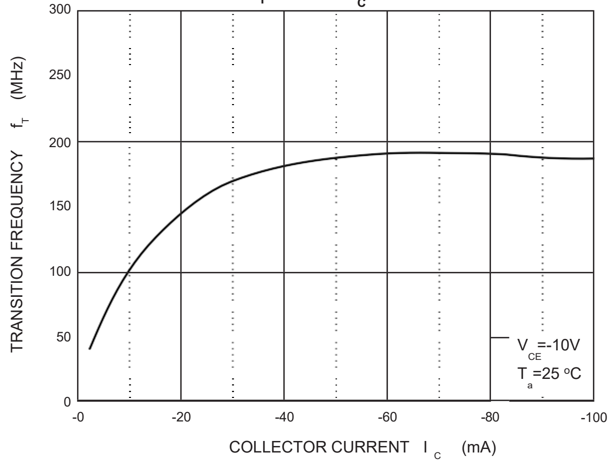
I_C — V_{BE}



C_{ob} / C_{ib} — V_{CB} / V_{EB}



f_T — I_C



P_c — T_a